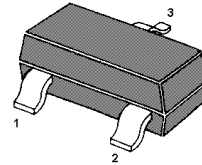


# MMBTSA1365

## PNP Silicon Epitaxial Planar Transistor

for high current drive application

The transistor is subdivided into three groups E, F and G according to its DC current gain.



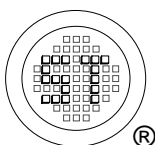
1.BASE 2.EMITTER 3.COLLECTOR  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	25	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	700	mA
Peak Collector Current	$-I_{CM}$	1	A
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 4\text{ V}$ , $-I_C = 100\text{ mA}$	E	$h_{FE}$	150	-	300	-
	F	$h_{FE}$	250	-	500	-
	G	$h_{FE}$	400	-	800	-
Collector Cutoff Current at $-V_{CB} = 25\text{ V}$	$-I_{CBO}$	-	-	1	$\mu\text{A}$	
Emitter Cutoff Current at $-V_{EB} = 2\text{ V}$	$-I_{EBO}$	-	-	1	$\mu\text{A}$	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	25	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	4	-	-	V	
Collector Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 25\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 6\text{ V}$ , $I_E = 10\text{ mA}$	$f_T$	-	180	-	MHz	

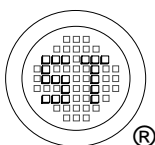
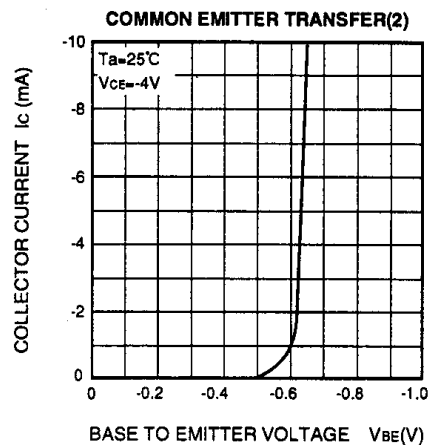
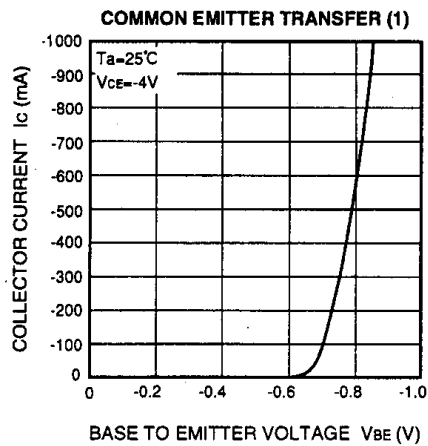
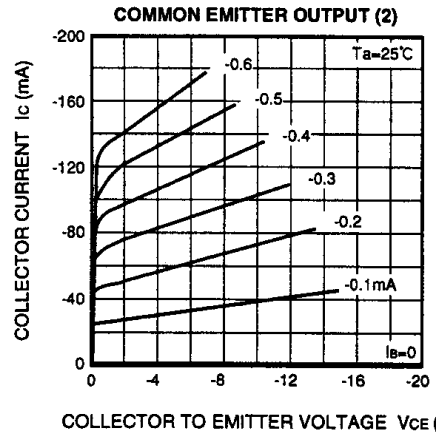
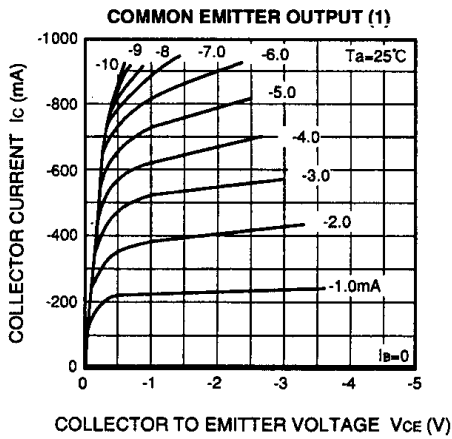
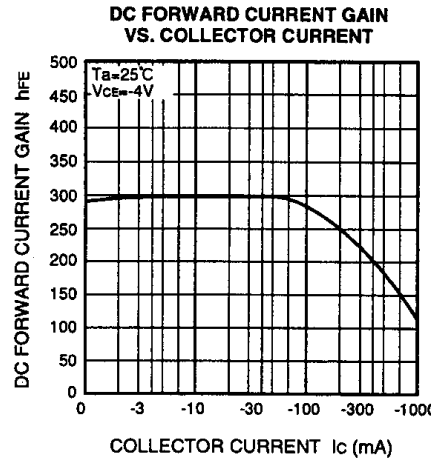
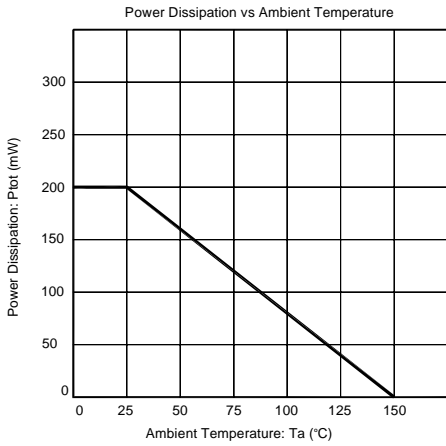


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Dated : 06/12/2006

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